

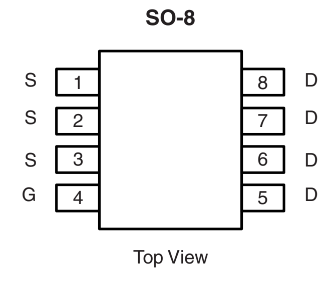
P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 30	0.042 at V_{GS} = - 10 V	- 5.7
	0.055 at V_{GS} = - 6 V	- 5.0
	0.070 at V_{GS} = - 4.5 V	- 4.4

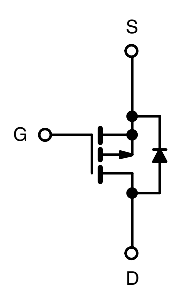
FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si9435BDY-T1-E3 (Lead (Pb)-free)
Si9435BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**10 s**	**Steady State**	**Unit**
Drain-Source Voltage		V_{DS}	- 30		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	- 5.7	- 4.1	A
	T_A = 70 °C		- 4.6	- 3.2	
Pulsed Drain Current		I_{DM}	- 30		
Continuous Source Current (Diode Conduction)[a]		I_S	- 2.3	- 1.1	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	2.5	1.3	W
	T_A = 70 °C		1.6	0.8	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 10 s	R_{thJA}	40	50	°C/W
	Steady State		70	95	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	24	30	

Notes:
a. Surface Mounted on 1" x 1" FR4 board.



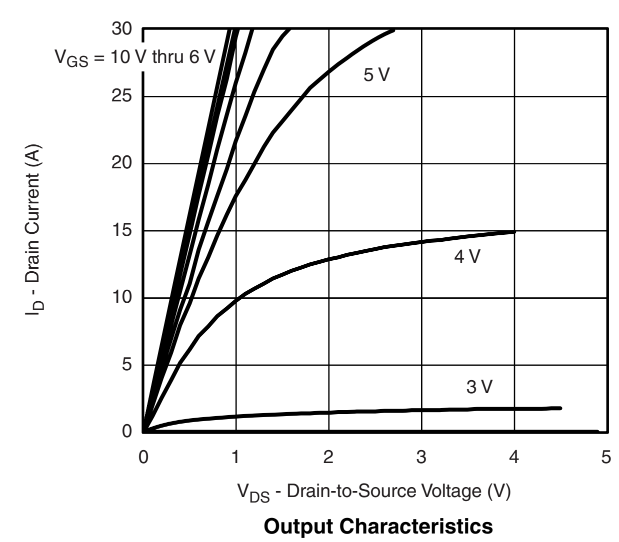
SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**[a]	**Max.**	**Unit**
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = - 250 µA	- 1.0		- 3.0	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 30 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 30 V, V_{GS} = 0 V, T_J = 70 °C			- 5	
On-State Drain Current[b]	$I_{D(on)}$	$V_{DS} \leq$ - 10 V, V_{GS} = - 10 V	- 20			A
		$V_{DS} \leq$ - 5 V, V_{GS} = - 4.5 V	- 5			
Drain-Source On-State Resistance[b]	$R_{DS(on)}$	V_{GS} = - 10 V, I_D = - 5.7 A		0.033	0.042	Ω
		V_{GS} = - 6 V, I_D = - 5 A		0.043	0.055	
		V_{GS} = - 4.5 V, I_D = - 4.4 A		0.056	0.070	
Forward Transconductance[b]	g_{fs}	V_{DS} = - 15 V, I_D = - 5.7 A		13		S
Diode Forward Voltage[b]	V_{SD}	I_S = - 2.3 A, V_{GS} = 0 V		- 0.8	- 1.1	V
Dynamic[a]						
Total Gate Charge	Q_g	V_{DS} = - 15 V, V_{GS} = - 10 V, I_D = - 3.5 A		16	24	nC
Gate-Source Charge	Q_{gs}			2.3		
Gate-Drain Charge	Q_{gd}			4.5		
Gate Resistance	R_g			8.8		Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 15 V, R_L = 15 Ω $I_D \cong$ - 1 A, V_{GEN} = - 10 V, R_g = 6 Ω		14	25	ns
Rise Time	t_r			14	25	
Turn-Off Delay Time	$t_{d(off)}$			42	70	
Fall Time	t_f			30	50	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = - 1.2 A, dI/dt = 100 A/µs		30	60	

Notes:
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

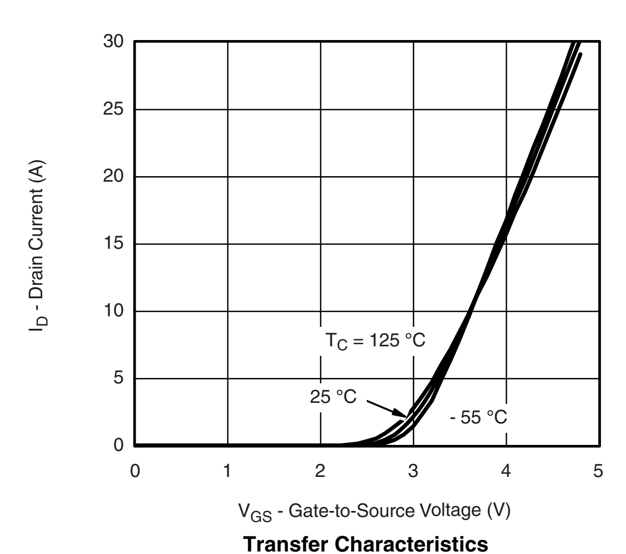
Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



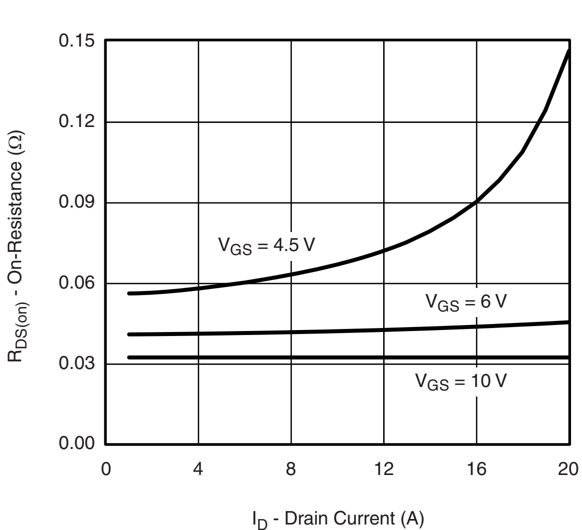
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



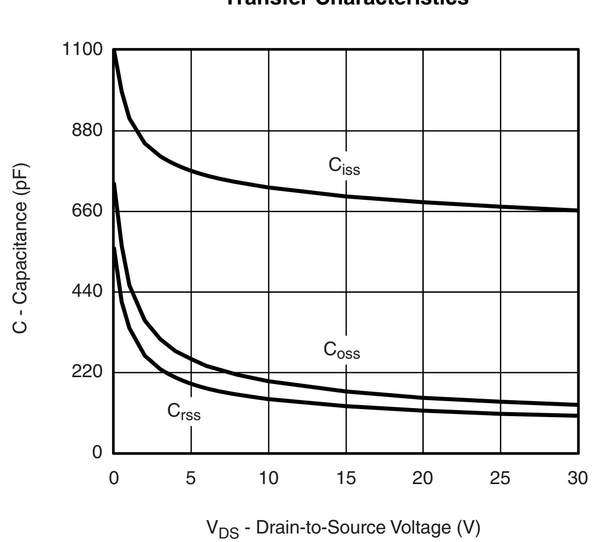
Output Characteristics



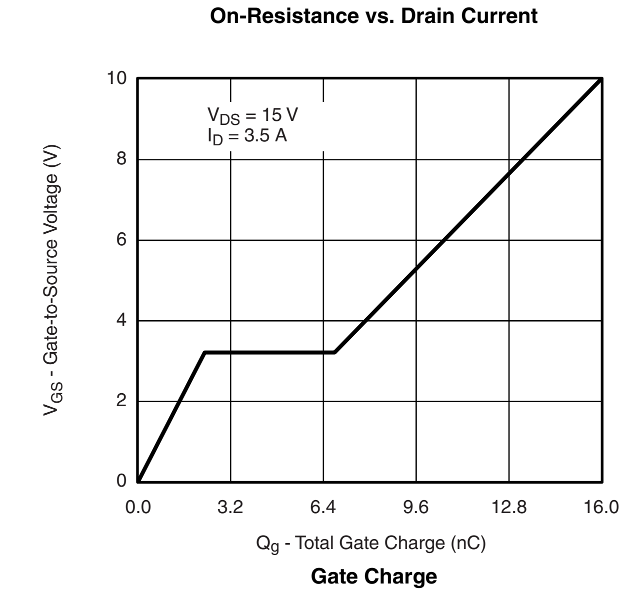
Transfer Characteristics



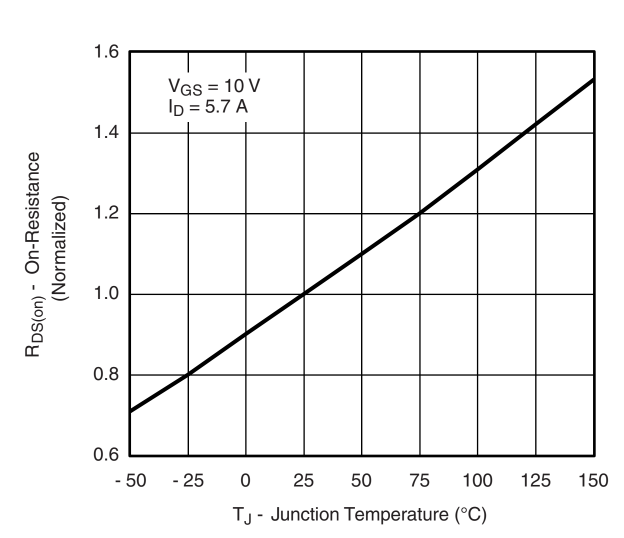
On-Resistance vs. Drain Current



Capacitance

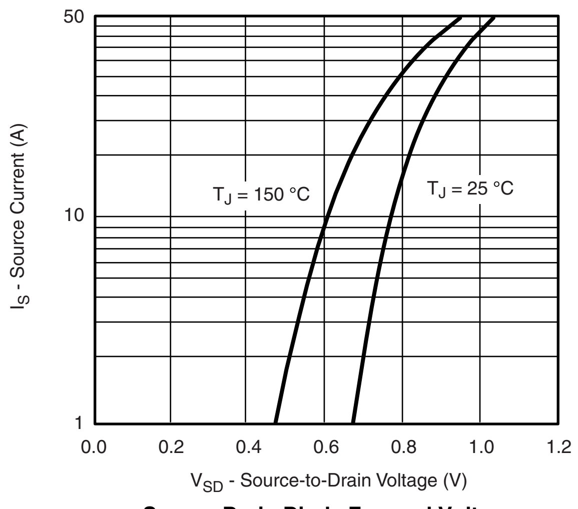


Gate Charge

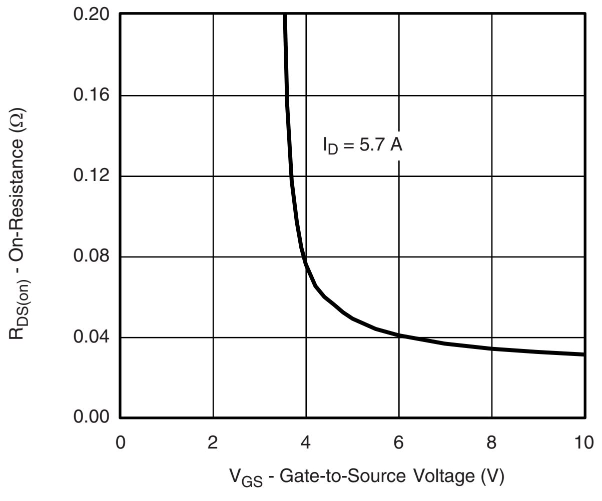


On-Resistance vs. Junction Temperature

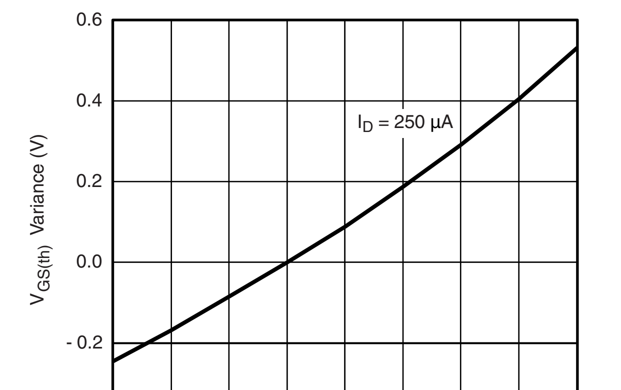
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



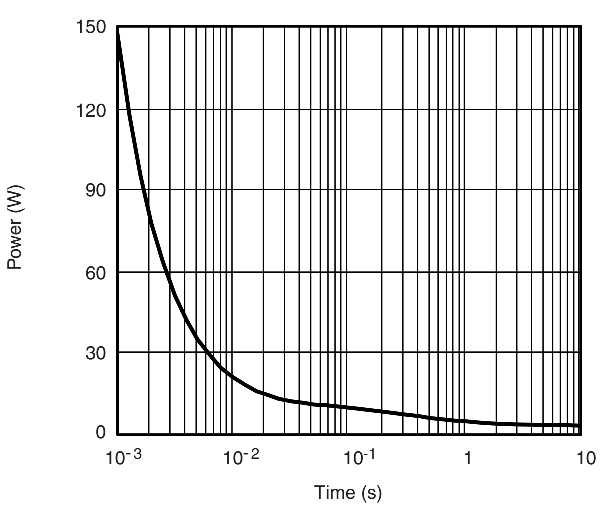
Source-Drain Diode Forward Voltage



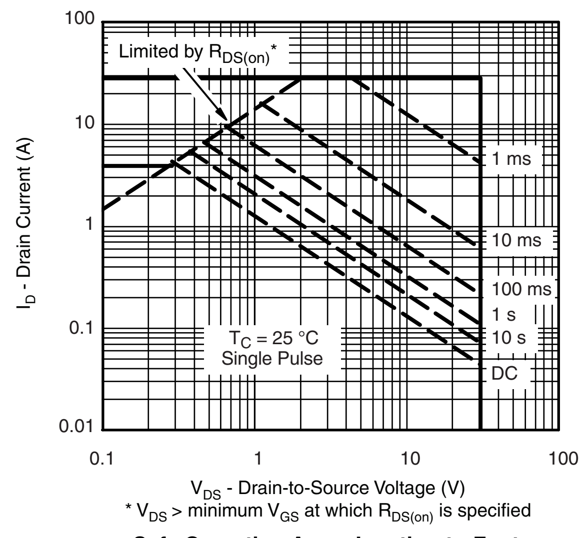
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

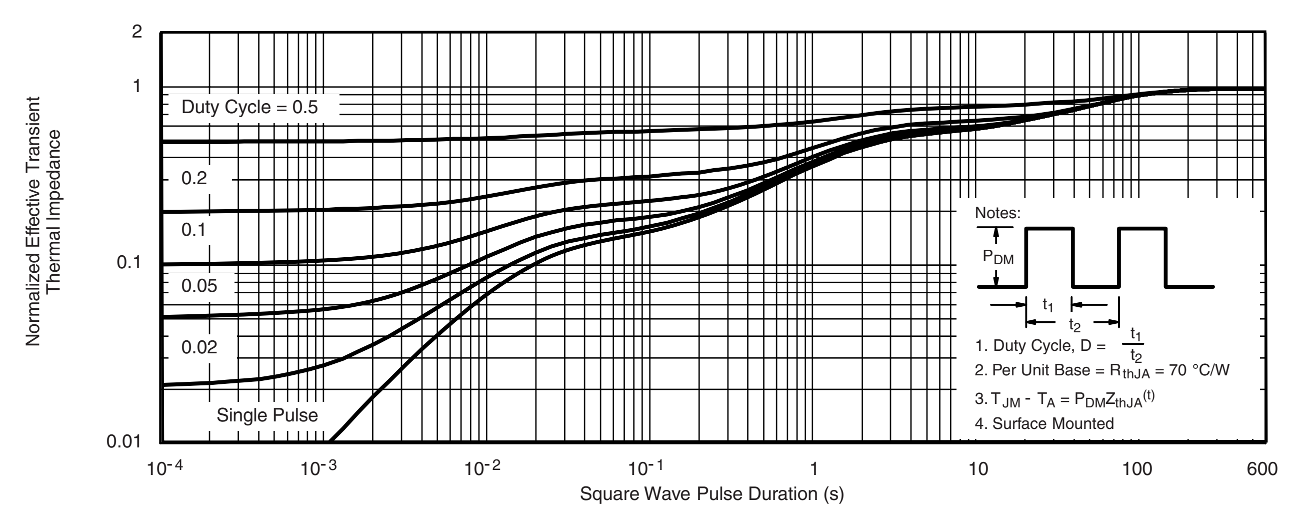


Single Pulse Power, Junction-to-Ambient

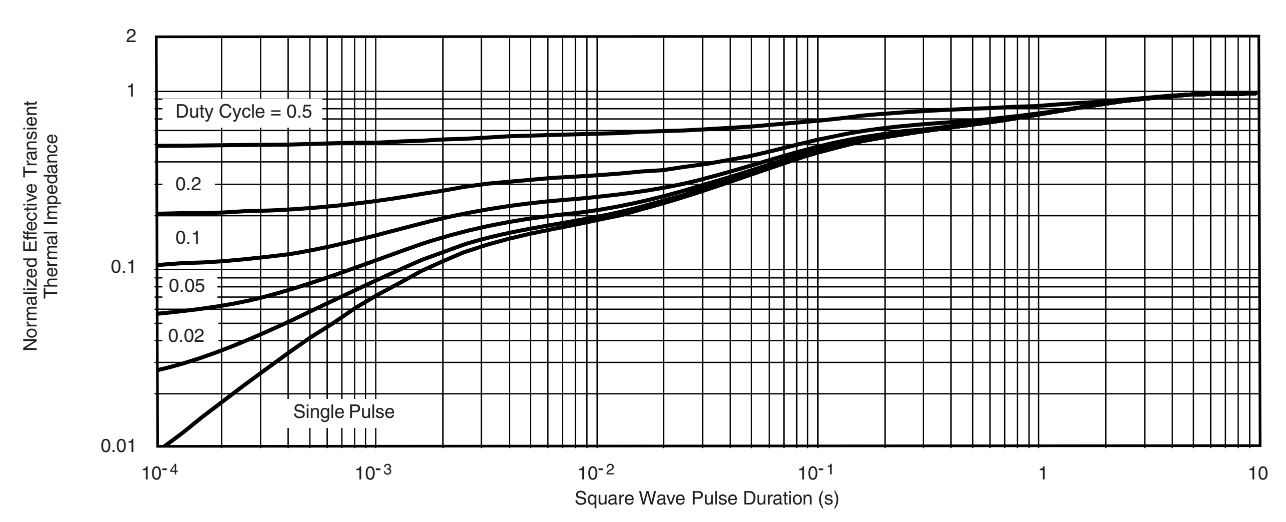


Safe Operating Area, Junction-to-Foot

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



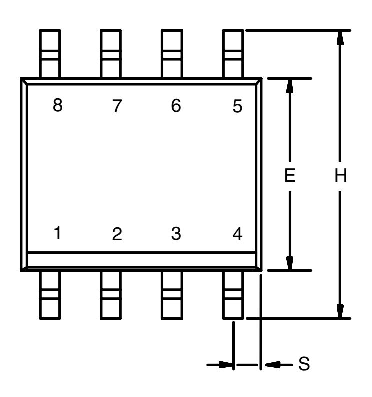
Normalized Thermal Transient Impedance, Junction-to-Ambient

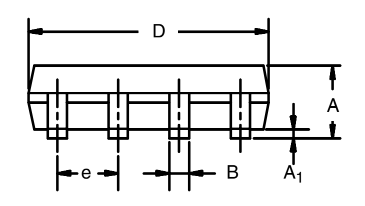


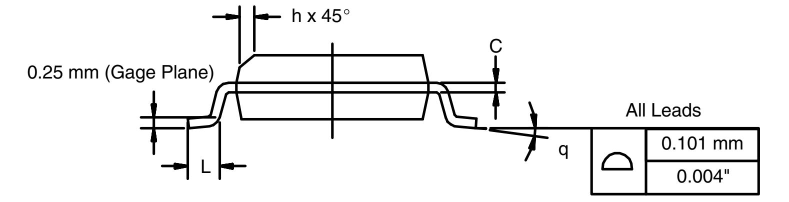
Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72245.

SOIC (NARROW): 8-LEAD
JEDEC Part Number: MS-012

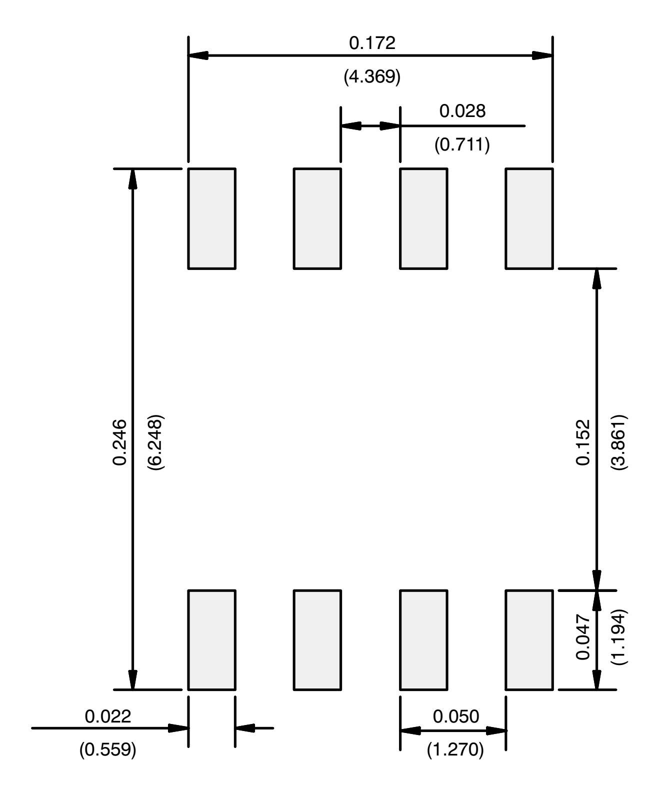






DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A_1	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

Return to Index

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay’s knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer’s responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer’s technical experts. Product specifications do not expand or otherwise modify Vishay’s terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.